MICROCHIP TC4426/TC4427/TC4428

1.5A Dual High-Speed Power MOSFET Drivers

Features:

- High Peak Output Current 1.5A
- Wide Input Supply Voltage Operating Range:
 - 4.5V to 18V
- High Capacitive Load Drive Capability 1000 pF in 25 ns (typ.)
- Short Delay Times 40 ns (typ.)
- · Matched Rise and Fall Times
- · Low Supply Current:
 - With Logic '1' Input 4 mA
 - With Logic '0' Input 400 μA
- Low Output Impedance 7Ω
- · Latch-Up Protected: Will Withstand 0.5A Reverse
- Input Will Withstand Negative Inputs Up to 5V
- ESD Protected 4 kV
- Pin-compatible with the TC426/TC427/TC428
- Space-saving 8-Pin MSOP and 8-Pin 6x5 DFN **Packages**

Applications:

- Switch Mode Power Supplies
- Line Drivers
- Pulse Transformer Drive

General Description:

The TC4426/TC4427/TC4428 are improved versions of the earlier TC426/TC427/TC428 family of MOSFET drivers. The TC4426/TC4427/TC4428 devices have matched rise and fall times when charging and discharging the gate of a MOSFET.

These devices are highly latch-up resistant under any conditions within their power and voltage ratings. They are not subject to damage when up to 5V of noise spiking (of either polarity) occurs on the ground pin. They can accept, without damage or logic upset, up to 500 mA of reverse current (of either polarity) being forced back into their outputs. All terminals are fully protected against Electrostatic Discharge (ESD) up to 4 kV.

The TC4426/TC4427/TC4428 MOSFET drivers can easily charge/discharge 1000 pF gate capacitances in under 30 ns. These devices provide low enough impedances in both the on and off states to ensure the MOSFET's intended state will not be affected, even by large transients.

Other compatible drivers are the TC4426A/TC4427A/ TC4428A family of devices. The TC4426A/TC4427A/ TC4428A devices have matched leading and falling edge input-to-output delay times, in addition to the matched rise and fall times of the TC4426/TC4427/ TC4428 devices.

NC

OUT A

OUT B

 V_{DD}

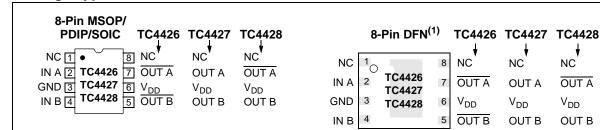
NC

OUT A

OUT B

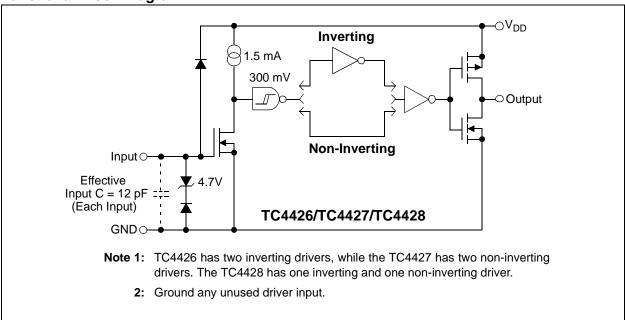
 V_{DD}

Package Types



Note 1: Exposed pad of the DFN package is electrically isolated.

Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Supply Voltage+22V
Input Voltage, IN A or IN B(V _{DD} + 0.3V) to (GND – 5V)
$\begin{array}{ccc} \text{Package Power Dissipation } (\text{T}_{\text{A}} \leq 70^{\circ}\text{C}) \\ \text{DFN} & & \text{Note 3} \\ \text{MSOP} & & 340 \text{ mW} \\ \text{PDIP} & & 730 \text{ mW} \\ \text{SOIC} & & 470 \text{ mW} \end{array}$
Storage Temperature Range65°C to +150°C
Maximum Junction Temperature+150°C

† Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

PIN FUNCTION TABLE

Name	Function					
NC	No Connection					
IN A	Input A					
GND	Ground					
IN B	Input B					
OUT B	Output B					
V_{DD}	Supply Input					
OUT A	Output A					
NC	No Connection					

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.										
Parameters	Sym	Min	Тур	Max	Units	Conditions				
Input										
Logic '1', High Input Voltage	V_{IH}	2.4	1		V	Note 2				
Logic '0', Low Input Voltage	V_{IL}	_		0.8	V					
Input Current	I _{IN}	-1.0		+1.0	μΑ	$0V \le V_{IN} \le V_{DD}$				
Output										
High Output Voltage	V _{OH}	V _{DD} – 0.025	l	_	V	DC Test				
Low Output Voltage	V_{OL}	_		0.025	V	DC Test				
Output Resistance	R _O	_	7	10	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Peak Output Current	I _{PK}	_	1.5	_	Α	V _{DD} = 18V				
Latch-Up Protection Withstand Reverse Current	I_{REV}		> 0.5	_	Α	Duty cycle \leq 2%, t \leq 300 μ s $V_{DD} = 18V$				
Switching Time (Note 1)						- 66				
Rise Time	t _R	_	19	30	ns	Figure 4-1				
Fall Time	t _F	_	19	30	ns	Figure 4-1				
Delay Time	t _{D1}	_	20	30	ns	Figure 4-1				
Delay Time	t _{D2}	_	40	50	ns	Figure 4-1				
Power Supply										
Power Supply Current	Is	_	_	4.5	mA	V _{IN} = 3V (Both inputs)				
		_	_	0.4		V _{IN} = 0V (Both inputs)				

- Note 1: Switching times ensured by design.
 - 2: For V temperature range devices, the V_{IH} (Min) limit is 2.0V.
 - **3:** Package power dissipation is dependent on the copper pad area on the PCB.

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise noted, over operating temperature range with $4.5V \le V_{DD} \le 18V$.										
Parameters	Sym	Min	Тур	Max	Units	Conditions				
Input										
Logic '1', High Input Voltage	V_{IH}	2.4	_	_	V	Note 2				
Logic '0', Low Input Voltage	V_{IL}	_	_	0.8	V					
Input Current	I _{IN}	-10	_	+10	μΑ	$0V \le V_{IN} \le V_{DD}$				
Output										
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	_	V	DC Test				
Low Output Voltage	V_{OL}	_	_	0.025	V	DC Test				
Output Resistance	R _O	_	9	12	Ω	I _{OUT} = 10 mA, V _{DD} = 18V				
Peak Output Current	I _{PK}	_	1.5	_	Α	V _{DD} = 18V				
Latch-Up Protection Withstand Reverse Current	I _{REV}	_	>0.5	_	Α	Duty cycle \leq 2%, t \leq 300 μ s $V_{DD} = 18V$				
Switching Time (Note 1)					•					
Rise Time	t _R	_	_	40	ns	Figure 4-1				
Fall Time	t _F	_	_	40	ns	Figure 4-1				
Delay Time	t _{D1}	_	_	40	ns	Figure 4-1				
Delay Time	t _{D2}	_	_	60	ns	Figure 4-1				
Power Supply					•					
Power Supply Current	I _S	_	=	8.0 0.6	mA	V _{IN} = 3V (Both inputs) V _{IN} = 0V (Both inputs)				

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$.										
Parameters	Sym	Min	Тур	Max	Units	Conditions				
Temperature Ranges										
Specified Temperature Range (C)	T _A	0	_	+70	°C					
Specified Temperature Range (E)	T _A	-40	_	+85	°C					
Specified Temperature Range (V)	T _A	-40	_	+125	°C					
Maximum Junction Temperature	TJ	_	_	+150	°C					
Storage Temperature Range	T _A	-65	_	+150	°C					
Package Thermal Resistances										
Thermal Resistance, 8L-6x5 DFN	θ_{JA}	_	33.2	_	°C/W					
Thermal Resistance, 8L-MSOP	θ_{JA}	_	206	_	°C/W					
Thermal Resistance, 8L-PDIP	θ_{JA}	_	125	_	°C/W					
Thermal Resistance, 8L-SOIC	θ_{JA}	_	155	_	°C/W					

^{2:} For V temperature range devices, the V_{IH} (Min) limit is 2.0V.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

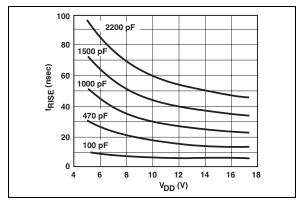


FIGURE 2-1: Rise Time vs. Supply Voltage.

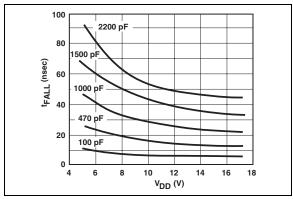


FIGURE 2-4: Fall Time vs. Supply Voltage.

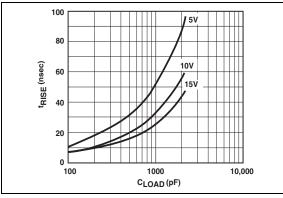


FIGURE 2-2: Rise Time vs. Capacitive Load.

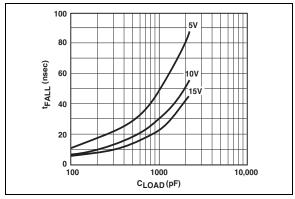


FIGURE 2-5: Fall Time vs. Capacitive Load.

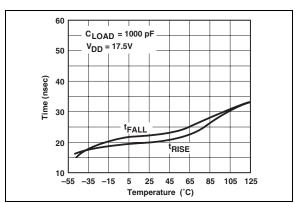


FIGURE 2-3: Rise and Fall Times vs. Temperature.

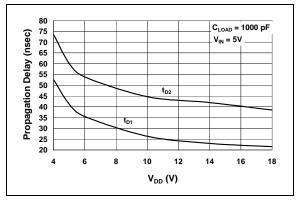


FIGURE 2-6: Propagation Delay Time vs. Supply Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

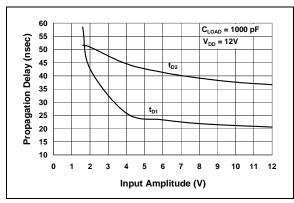


FIGURE 2-7: Propagation Delay Time vs. Input Amplitude.

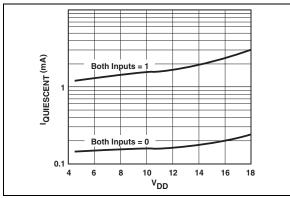


FIGURE 2-8: Supply Current vs. Supply Voltage.

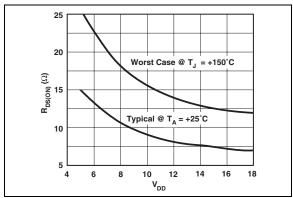


FIGURE 2-9: Output Resistance (R_{OH}) vs. Supply Voltage.

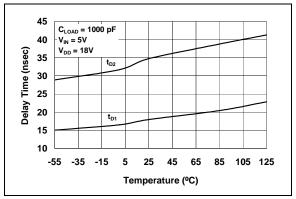


FIGURE 2-10: Propagation Delay Time vs. Temperature.

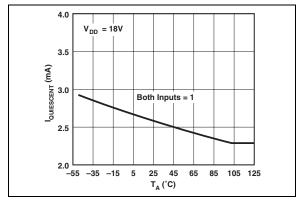


FIGURE 2-11: Supply Current vs. Temperature.

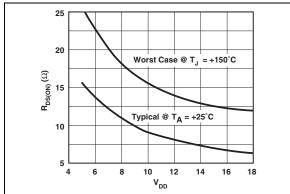


FIGURE 2-12: Output Resistance (R_{OL}) vs. Supply Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

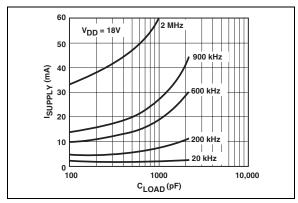


FIGURE 2-13: Supply Current vs. Capacitive Load.

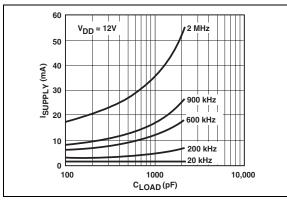


FIGURE 2-14: Supply Current vs. Capacitive Load.

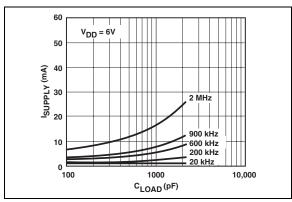


FIGURE 2-15: Supply Current vs. Capacitive Load.

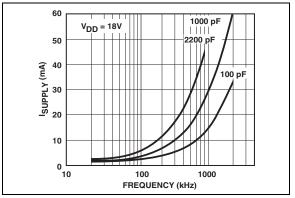


FIGURE 2-16: Supply Current vs. Frequency.

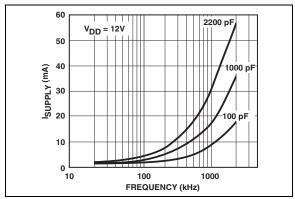


FIGURE 2-17: Supply Current vs. Frequency.

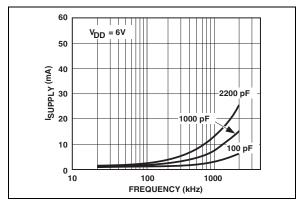


FIGURE 2-18: Supply Current vs. Frequency.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

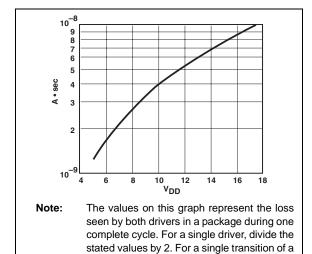


FIGURE 2-19: Crossover Energy vs. Supply Voltage.

single driver, divide the stated value by 4.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE (1)

8-Pin PDIP/ MSOP/SOIC	8-Pin DFN	Symbol	Description
1	1	NC	No connection
2	2	IN A	Input A
3	3	GND	Ground
4	4	IN B	Input B
5	5	OUT B	Output B
6	6	V_{DD}	Supply input
7	7	OUT A	Output A
8	8	NC	No connection
_	PAD	NC	Exposed Metal Pad

Note 1: Duplicate pins must be connected for proper operation.

3.1 Inputs A and B

MOSFET driver inputs A and B are high-impedance, TTL/CMOS compatible inputs. These inputs also have 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

3.2 Ground (GND)

Ground is the device return pin. The ground pin(s) should have a low-impedance connection to the bias supply source return. High peak currents will flow out the ground pin(s) when the capacitive load is being discharged.

3.3 Output A and B

MOSFET driver outputs A and B are low-impedance, CMOS push-pull style outputs. The pull-down and pull-up devices are of equal strength, making the rise and fall times equivalent.

3.4 Supply Input (V_{DD})

The V_{DD} input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pin. The V_{DD} input should be bypassed with local ceramic capacitors. The value of these capacitors should be chosen based on the capacitive load that is being driven. A value of 1.0 μF is suggested.

3.5 Exposed Metal Pad

The exposed metal pad of the 6x5 DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a printed circuit board, to aid in heat removal from the package.

4.0 APPLICATIONS INFORMATION

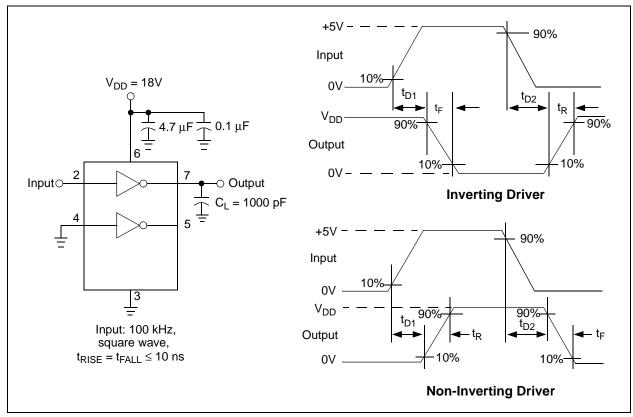


FIGURE 4-1: Switching Time Test Circuit.

5.0 PACKAGING INFORMATION

5.1 Package Marking Information

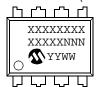
8-Lead DFN



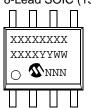
8-Lead MSOP



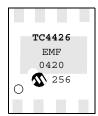
8-Lead PDIP (300 mil)



8-Lead SOIC (150 mil)



Example:



Example:



Example:







Legend: XX...X Customer specific information*

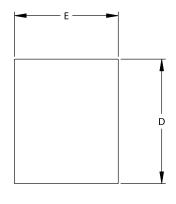
Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

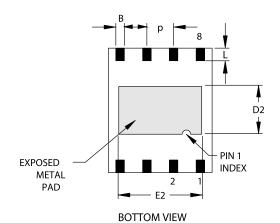
NNN Alphanumeric traceability code

ote: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line thus limiting the number of available characters for customer specific information.

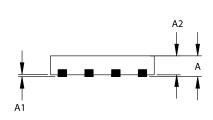
* Standard device marking consists of Microchip part number, year code, week code, and traceability code.

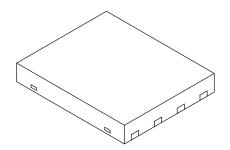
8-Lead Plastic Dual Flat No Lead Package (MF) 6x5 mm Body (DFN-S) - Saw Singulated





TOP VIEW





	Units		INCHES		М		
Dimension Li	mits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.050 BSC			1.27 BSC	
Overall Height	Α	.033	.035	.037	0.85	0.90	0.95
Package Thickness	A2	.031	.035	.037	0.80	0.89	0.95
Standoff	A1	.000	.0004	.002	0.00	0.01	0.05
Base Thickness	A3	.007	.008	.009	0.17	0.20	0.23
Overall Length	E	.195	.197	.199	4.95	5.00	5.05
Exposed Pad Length	E2	.152	.157	.163	3.85	4.00	4.15
Overall Width	D	.234	.236	.238	5.95	6.00	6.05
Exposed Pad Width	D2	.089	.091	.093	2.25	2.30	2.35
Lead Width	В	.014	.016	.019	0.35	0.40	0.47
Lead Length	L	.024		.026	0.60		0.65

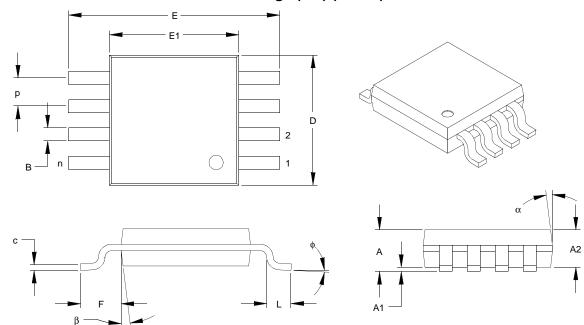
Notes:

JEDEC equivalent: MO-220

Drawing No. C04-122

Revised 11/3/03

8-Lead Plastic Micro Small Outline Package (MS) (MSOP)



	Units	INCHES			MI		
Dimension Lim	its	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.026 BSC			0.65 BSC	
Overall Height	А	-	-	.043	-	-	1.10
Molded Package Thickness	A2	.030	.033	.037	0.75	0.85	0.95
Standoff	A1	.000	-	.006	0.00	-	0.15
Overall Width	Е	.193 BSC			4.90 BSC		
Molded Package Width	E1		.118 BSC		3.00 BSC		
Overall Length	D		.118 BSC		3.00 BSC		
Foot Length	L	.016	.024	.031	0.40	0.60	0.80
Footprint (Reference)	F		.037 REF		0.95 REF		
Foot Angle	ф	0°	-	8°	0°	-	8°
Lead Thickness	С	.003	.006	.009	0.08	-	0.23
Lead Width	В	.009	.012 .016		0.22	-	0.40
Mold Draft Angle Top	α	5°	1	15°	5°	-	15°
Mold Draft Angle Bottom	β	5°	ı	15°	5°	-	15°

^{*} Controlling Parameter

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

See ASME Y14.5M

REF: Reference Dimension, usually without tolerance, for information purposes only.

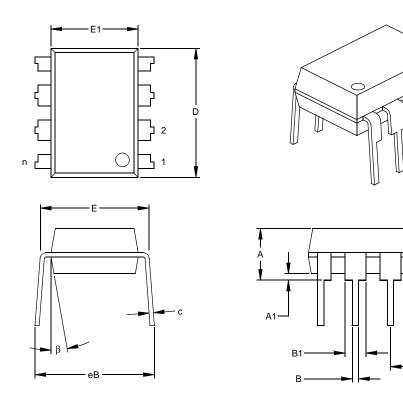
See ASME Y14.5M

JEDEC Equivalent: MO-187

Drawing No. C04-111

Revised 07-21-05

8-Lead Plastic Dual In-line (P) - 300 mil (PDIP)



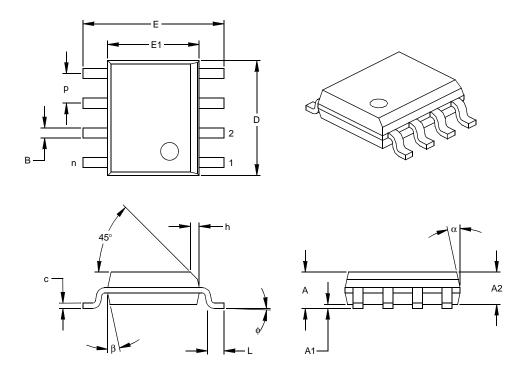
	Units	INCHES*			MILLIMETERS		
Dimension	Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	Α	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	Е	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	В	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing §	eВ	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15
* Controlling Dozemates	β	5	10	15	5	10	1:

* Controlling Parameter § Significant Characteristic

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC Equivalent: MS-001 Drawing No. C04-018

8-Lead Plastic Small Outline (SN) - Narrow, 150 mil (SOIC)



	Units		INCHES*		MILLIMETERS		
Dimension	MIN	NOM	MAX	MIN	NOM	MAX	
Number of Pins	n		8			8	
Pitch	р		.050			1.27	
Overall Height	Α	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	E	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	ф	0	4	8	0	4	8
Lead Thickness	С	.008	.009	.010	0.20	0.23	0.25
Lead Width	В	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

^{*} Controlling Parameter

Notes

 $Dimensions\ D\ and\ E1\ do\ not\ include\ mold\ flash\ or\ protrusions.\ Mold\ flash\ or\ protrusions\ shall\ not\ exceed\ .010"\ (0.254mm)\ per\ side.$

JEDEC Equivalent: MS-012

Drawing No. C04-057

[§] Significant Characteristic

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	x xx	xxx	¥	Ex	amples:	
•	 erature Package nge	Tape & Reel	PB Free	a)	TC4426COA:	1.5A Dual Inverting MOSFET driver, 0°C to +70°C SOIC package.
Device:	TC4427: 1.5A Dua	MOSFET Driver, MOSFET Driver, MOSFET Driver,	Non-Inverting	b)	TC4426EUA:	1.5A Dual Inverting MOSFET driver, -40°C to +85°C. MSOP package.
Temperature Range:	C = 0°C to + E = -40°C to + V = -40°C to +		SOIC only)	c)	TC4426EMF:	1.5A Dual Inverting MOSFET driver, -40°C to +85°C, DFN package.
Package:	MF713 = Dual, Flat, (Tape and OA = Plastic SC		m Body), 8-lead), 8-lead	a)	TC4427CPA:	1.5A Dual Non-Inverting MOSFET driver, 0°C to +70°C PDIP package.
		P (300 mil Body), 8 cro Small Outline (cro Small Outline (MSOP), 8-lead	b)	TC4427EPA:	1.5A Dual Non-Inverting MOSFET driver, -40°C to +85°C PDIP package.
				a)	TC4428COA713	:1.5A Dual Complementary MOSFET driver, 0°C to +70°C, SOIC package, Tape and Reel.
				b)	TC4428EMF:	1.5A Dual Complementary, MOSFET driver, -40°C to +85°C DFN package.

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